

NEC
ELECTRONIC INSTRUMENTS

MOS INTEGRATED CIRCUIT **μPD3593**

2048-BIT CCD LINEAR IMAGE SENSOR WITH PERIPHERAL CIRCUITS

The μPD3593 is a 2048-bit high sensitivity CCD (Charge Coupled Device) linear image sensor which changes optical images to electrical signal.

The μPD3593 has an output amplifier which has wide output range, and which can switch gain. Therefore it is easy to get signal level which is easy to process from low illumination to high illumination, and it is easy to apply to many purposes.

With internal generation circuit of driving signal and internal driver, the μPD3593 performs only with two basic clock inputs. No special driving circuit is required. In addition, analog signal processor convert and output independent CCD register in every bit to continuous video signal. So it is easy to interface to A/D converter or Bi-level converter.

FEATURES

• Valid photocell	2 048-bit
• Photocell's pitch	14 μ m
• CCD output	4 steps selectable gain (2, 4, 8, 16 times)
• Peak response wavelength	550 nm (green)
• Resolution	8 dot/mm across the shorter side of a B4-size (257 x 364 mm) sheet
• Power supply	+12 V, +5 V
• Drive clock level	CMOS 5 V clock input x 2
• High speed scan	1 ms/line
• Built-in circuit	Timing generator CCD clock driver Optical black clamp circuit Sample and hold circuit 4-step variable gain amplifier

ORDERING INFORMATION

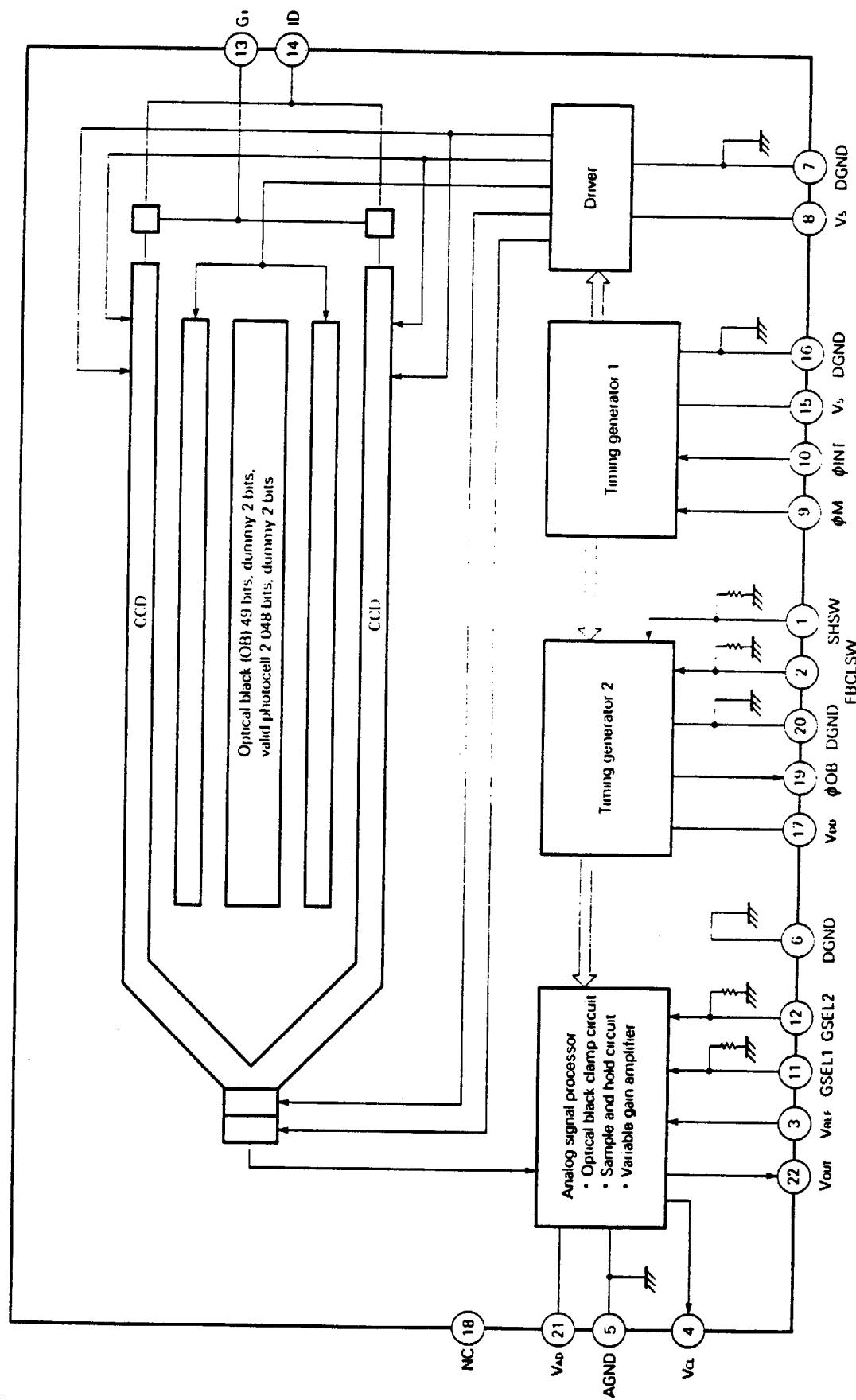
Part Number	Package	Quality Grade
μPD3593D	22-pin ceramic DIP (CERDIP) (400 mil)	Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

The information in this document is subject to change without notice.

BLOCK DIAGRAM

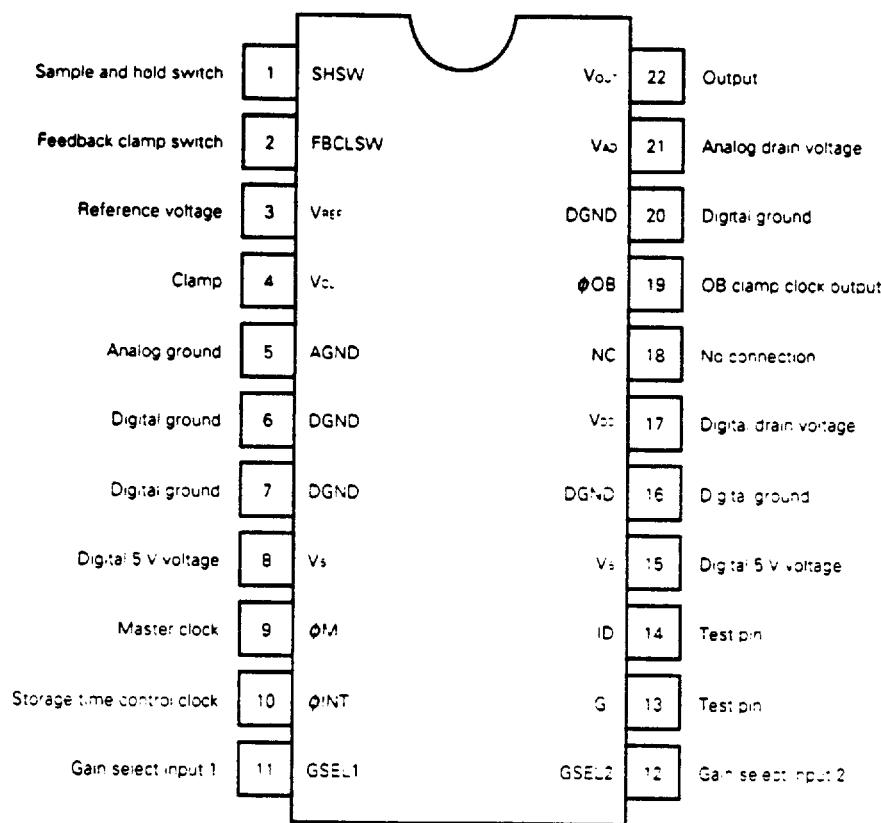
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DB3593

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PIN CONFIGURATION (Top View)



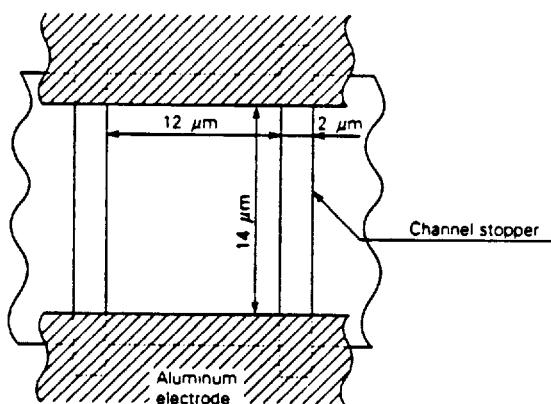
Function of SHSW pin

SHSW	Sample and hold circuit
V _S	Stop
0 V	Operate

Function of FBCLSW pin

FBCLSW	Feedback clamp circuit
V _S	Stop
0 V	Operate

PHOTOCELL STRUCTURE DIAGRAM



PIN FUNCTIONS

Pin No.	Symbol	Functions
1	SHSW	<p>Internal sample and hold enable pin.</p> <p>Low level input: Internal sample and hold circuit operates.</p> <p>High level input: Internal sample and hold circuit stops and signal from CCD is output just as it is. This pin is connected internally to pull-down resistor (refer to electrical characteristics to obtain pull-down resistance). Therefore, when internal sample and hold circuit is used, this pin can be left unconnected.</p>
2	FBCLSW	<p>Internal optical black clamp enable pin.</p> <p>Low level input: Internal optical black clamp circuit operates.</p> <p>High level input: Internal optical black clamp circuit stops.</p> <p>This pin is connected internally to pull-down resistor (refer to electrical characteristics to obtain pull-down resistance). Therefore, when internal optical black clamp circuit is used, this pin can be left unconnected.</p>
Optical black clamp equivalent circuit		
Connecting external capacitor to Vcl (pin 4), fix hold time according to the charge time.		
3	VREF	Reference voltage input pin for internal optical black clamp circuit.
4	Vcl	<p>Connected to capacitor which sets hold time constant for internal optical black clamp circuit.</p> <p>Leak path resistance of internal capacitor (about 250 pF) will be 2 or 3 MΩ, therefore, when charge time is needed more than 1 ms, use external capacitor.</p> <p>When optical black clamp level precision is needed, this pin is input pin of feed back signal from external high precision comparator.</p> <p>Refer to parameter of clamp error in electrical characteristics to obtain dispersion of clamp level when internal comparator is used.</p>
5	AGND	Ground pin for analog signal processing unit (optical black clamp circuit, sample and hold circuit).
6	DGND	Ground pin for digital circuits (timing generator unit).
7	DGND	Ground pin for digital circuits (driver unit).
8	Vs	+5 V power supply pin for digital circuits.

Pin No.	Symbol	Functions															
9	ϕM	Master clock input pin. Data rate is 1/2 of master clock frequency.															
10	ϕINT	Control clock input pin to set charge time. By inputting this signal, optical black signal is output from 26 clock pulses after ϕM (Refer to timing chart to obtain detailed timing).															
11	GSEL1	By combining these 2 pins, output amplifier circuit gain can be selected.															
12	GSEL2	<table border="1" style="margin-left: auto; margin-right: auto;"> <thead> <tr> <th>GSEL1</th> <th>GSEL2</th> <th>output amplifier circuit gain</th> </tr> </thead> <tbody> <tr> <td>L</td> <td>L</td> <td>2 times</td> </tr> <tr> <td>L</td> <td>H</td> <td>4 times</td> </tr> <tr> <td>H</td> <td>L</td> <td>8 times</td> </tr> <tr> <td>H</td> <td>H</td> <td>16 times</td> </tr> </tbody> </table>	GSEL1	GSEL2	output amplifier circuit gain	L	L	2 times	L	H	4 times	H	L	8 times	H	H	16 times
GSEL1	GSEL2	output amplifier circuit gain															
L	L	2 times															
L	H	4 times															
H	L	8 times															
H	H	16 times															
<p>These pins are connected internally to pull-down resistor (refer to electrical characteristics to obtain pull-down resistance). Therefore, when using at input low level, this pin can be left unconnected.</p>																	
13	G1	Test pin. Connect to digital ground.															
14	ID	Test pin. Connect to +5 V power supply.															
15	V _S	+5 V power supply pin for digital circuit.															
16	DGND	Ground pin for digital circuit (timing generator unit).															
17	V _{DD}	+12 V power supply pin for digital circuit.															
18	NC	Non connect pin. Leave this pin unconnected or connect to digital GND.															
19	ϕOB	Output pin for optical black clamp pulse. CMOS output under 5 V operation.															
20	DGND	Ground pin for digital circuit (timing generator unit).															
21	V _{AD}	+12 V power supply pin for analog circuit.															
22	V _{OUT}	Output pin. Refer to timing chart to obtain detailed output timing.															

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Analog drain voltage	V_{AD}	-0.3 ~ +15	V
Digital drain voltage	V_{DD}	-0.3 ~ +15	V
Test pin ID voltage	V_{ID}	-0.3 ~ +15	V
Digital 5 V voltage	V_S	-0.3 ~ +7	V
Reference voltage	V_{REF}	-0.3 ~ +7	V
Clamp pin input voltage	V_{CL}	-0.3 ~ +7	V
Sample and hold switch	V_{SHSW}	V_S	V
Feedback clamp switch	V_{FBCLSW}	V_S	V
Master clock voltage	V_{OM}	V_S	V
Storage time control clock voltage	V_{INT}	V_S	V
Gain select input voltage 1	V_{GSEL1}	V_S	V
Gain select input voltage 2	V_{GSEL2}	V_S	V
Operating ambient temperature	T_{OPR}	-25 ~ +60	$^\circ\text{C}$
Storage temperature	T_{STG}	-40 ~ +100	$^\circ\text{C}$

RECOMMENDED OPERATING CONDITIONS ($T_A = -25$ to $+60^\circ\text{C}$)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Analog drain voltage	V_{AD}	11.4	12.0	12.6	V
Digital drain voltage	V_{DD}	11.4	12.0	12.6	V
Test pin ID voltage	V_{ID}	11.4	12.0	12.6	V
Digital 5 V voltage	V_S	4.5	5.0	5.5	V
Reference voltage	V_{REF}	4.0	4.5	5.0	V
Master clock ϕM signal high level	V_{OMH}	4.5	V_S	V_S	V
Master clock ϕM signal low level	V_{OML}	-0.3	0	0.5	V
Storage time control clock ϕINT signal high level	V_{INTH}	4.5	V_S	V_S	V
Storage time control clock ϕINT signal low level	V_{INTL}	-0.3	0	0.5	V
Gain select input voltage GSEL 1,2 signal high level	V_{GSELH}	4.5	V_S	V_S	V
Gain select input voltage GSEL 1,2 signal low level (Note 1)	V_{GSELL}	-0.3	0	0.5	V
Sample and hold switch SHSW signal high level	V_{SHH}	4.5	V_S	V_S	V
Sample and hold switch SHSW signal low level (Note 1)	V_{SHL}	-0.3	0	0.5	V
Feedback clamp switch FBCLSW signal high level	V_{FBCLH}	4.5	V_S	V_S	V
Feedback clamp switch FBCLSW signal low level (Note 1)	V_{FBCLL}	-0.3	0	0.5	V
Hold capacitor (Note 2)	C_H	—	0.001	0.01	μF
Master clock ϕM frequency	freq	0.5	2	4	MHz

Note 1. Gain select pin (GSEL 1, 2), sample and hold switch pin (SHSW), feedback clamp switch pin (FBCLSW) are pull down to GND internally with $50\text{ k}\Omega$ ~ $200\text{ k}\Omega$ resistor.

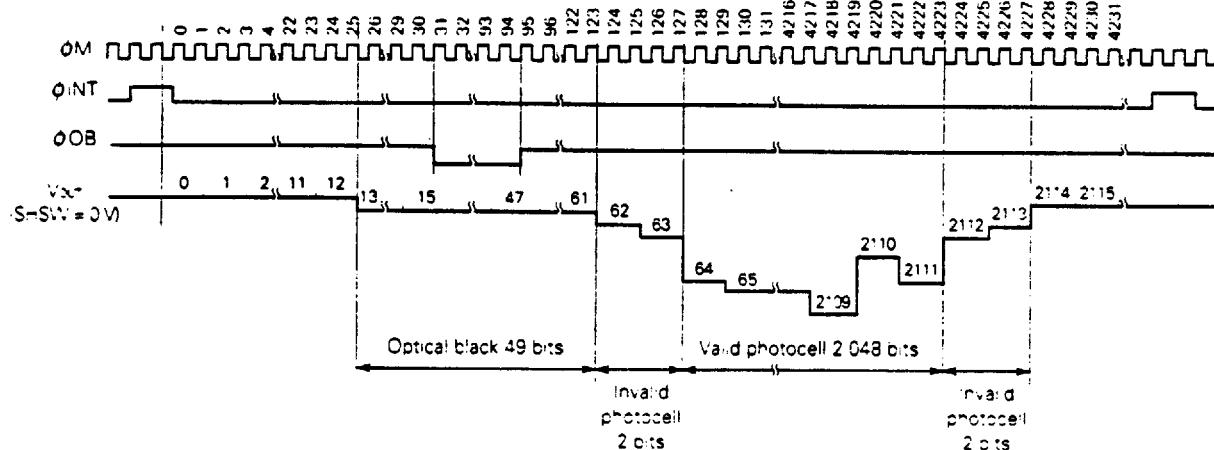
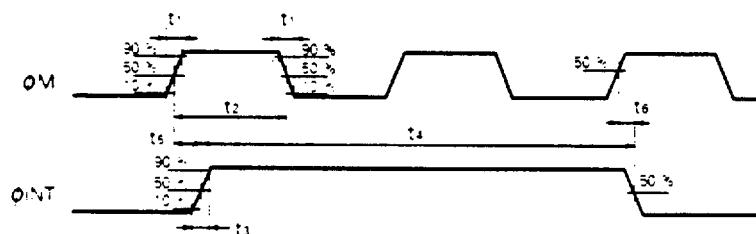
2. Control voltage hold capacitor depending on storage time (T_{INT}).

ELECTRICAL CHARACTERISTICS $T_c = +25^\circ\text{C}$, $V_{AD} = V_{DD} = 12 \text{ V}$, $V_s = 5 \text{ V}$, $f_{\text{DM}} = 2 \text{ MHz}$, data rate = 1 MHz, storage time = 10msinput signal clock = 5 Vpp, $V_{REF} = 4.5 \text{ V}$, light source = 3200 K halogen lamp + C500 (infrared cut filter)

Parameter	Symbol	Test Conditions			MIN.	TYP.	MAX.	Unit	Built-in amplifier gain
			GSEL1	GSEL2					
Saturation voltage	V_{SAT}	Daylight color fluorescent lamp	—	—	2	3	—	V	
Saturation exposure	SE	Daylight color fluorescent lamp	0	0	—	0.114	—	lx·s	x2
			0	1	—	0.051	—		x4
			1	0	—	0.027	—		x8
			1	1	—	0.012	—		x16
Photo response non-uniformity	$PRNU$	$V_{OUT} = 500 \text{ mV}$	0	0	—	± 4	± 8	%	x2
Average dark signal	ADS	$T_c = 25^\circ\text{C}$ Note, $T_{INT} = 10 \text{ ms}$ light shielding	0	0	—	1	5	mV	x2
			0	1	—	2	10		x4
			1	0	—	4	20		x8
			1	1	—	8	40		x16
Dark signal non-uniformity	DSNU	$T_c = 25^\circ\text{C}$ Note, $T_{INT} = 10 \text{ ms}$ light shielding	0	0	-5	± 1	± 5	mV	x2
			0	1	-10	± 2	± 10		x4
			1	0	-20	± 4	± 20		x8
			1	1	-40	± 8	± 40		x16
Power consumption	P_w	$V_{DD} = V_{DD} = 12 \text{ V}$	0	0	150	230	350	mW	
		$V_s = 5 \text{ V}$, $f_{\text{DM}} = 2 \text{ MHz}$	1	1	80	120	180		
Output impedance	Z_o		0	0	—	1	2	kΩ	
Response	R _f	Daylight color fluorescent lamp	0	0	18.5	26.4	34.3		x2
			0	1	—	59.4	—	V/lx·s	x4
			1	0	—	110	—		x8
			1	1	—	248	—		x16
Response peak wavelength			—	—	—	550	—	nm	
Image lag	IL	$V_{OUT} = 1 \text{ V}$	0	0	—	2	5	%	x2
Reference voltage input current	I_{REF}		0	0	—	0.001	0.1	mA	
Transfer efficiency	TTE	$V_{OUT} = 500 \text{ mV}$	0	0	92	98	—	%	x2
Sample and hold noise	SHN	light shielding	0	0	—	15	30	mV	x2
Clamp error	V _{ERR}	light shielding $V_{REF} = 4.5 \text{ V}$	0	0	-100	0	± 100	mV	x2
Clock input capacitance Master clock input pin Storage time control clock input pin	C _φ		—	—	—	5	10	pF	
Pull down resistor Gain select input pin Sample and hold switch pin Feedback clamp switch pin	R _{PD}	$V_{IN} = 5 \text{ V}$	—	—	50	100	200	kΩ	
Register imbalance	RI	$V_{OUT} = 500 \text{ mV}$	0	0	—	—	3	%	x2
Dynamic range	DR	$V_{SAT}/DSNU$	0	0	—	3000	—		x2
			0	1	—	1500	—	times	x4
			1	0	—	750	—		x8
			1	1	—	375	—		x16

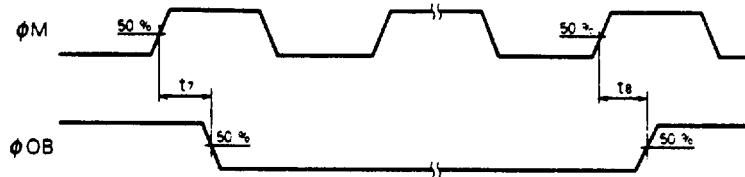
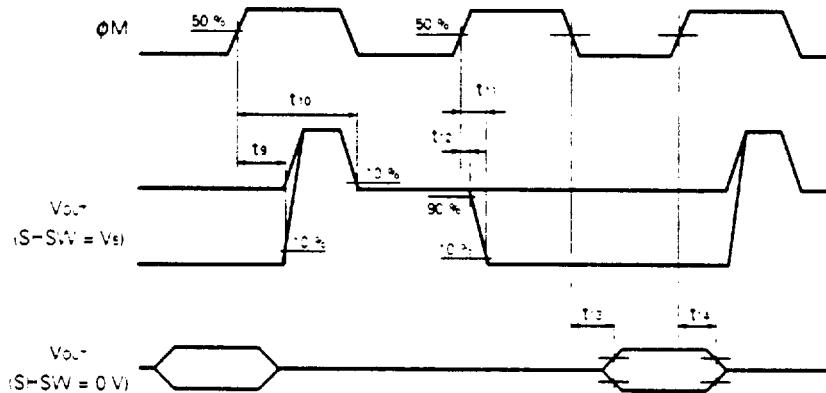
Note T_c = Case temperature

TIMING CHART

Timing Chart for ΦM and ΦINT 

Recommended Timing (Unit: ns)

Parameter	MIN.	TYP.	MAX.
t_1	0	20	100
t_2	125	250	1000
t_3	0	20	100
t_4	—	$4t_2$	—
t_5	-30	0	t_2
t_6	$-t_2$	0	t_2

φOB Signal Delay from φM**Vout Signal Delay from φM****Signal Delay Time (Vout = 500 mV, output amplifier gain: x2)**

(Unit: ns)

Parameter	MIN.	TYP.	MAX.
t_7	200	280	370
t_8	150	220	290
t_9	40	60	80
t_{10}	160	230	300
t_{11}	66	95	125
t_{12}	40	60	80
t_{13}		80	120
t_{14}		50	100

DEFINITIONS OF CHARACTERISTIC ITEMS

1. Saturation voltage: VSAT

Output signal voltage at which the response linearity is lost.

2. Saturation exposure: SE

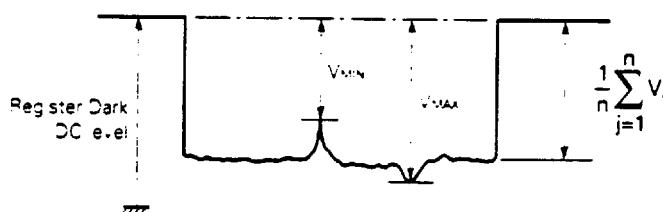
Product of intensity of illumination (I_x) and storage time (s) when saturation of output voltage occurs.

3. Photo response non-uniformity: PRNU

The peak/bottom ratio to the average output voltage of all the valid bits calculated by the following formula.

$$\text{PRNU (\%)} = \left(\frac{V_{\text{MAX. or } V_{\text{MIN.}}}}{\frac{1}{n} \sum_{j=1}^n V_j} - 1 \right) \times 100$$

n : Number of valid bits
V_j : Output voltage of each bit



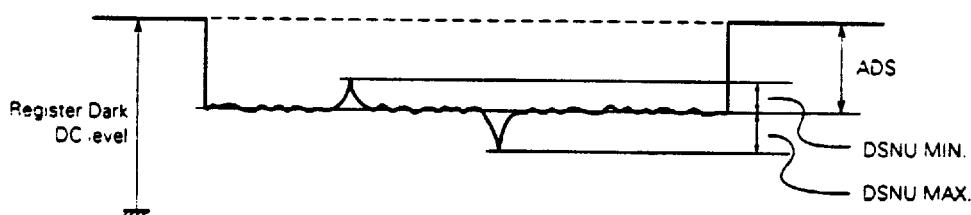
4. Average dark signal: ADS

Output average voltage in light shielding

$$\text{ADS(mV)} = \frac{1}{n} \sum_{j=1}^n V_j$$

5. Dark signal non-uniformity: DSNU

The difference between peak or bottom output voltage in light shielding and ADS.



6. Output impedance: Z_O

Output pin impedance viewed from outside.

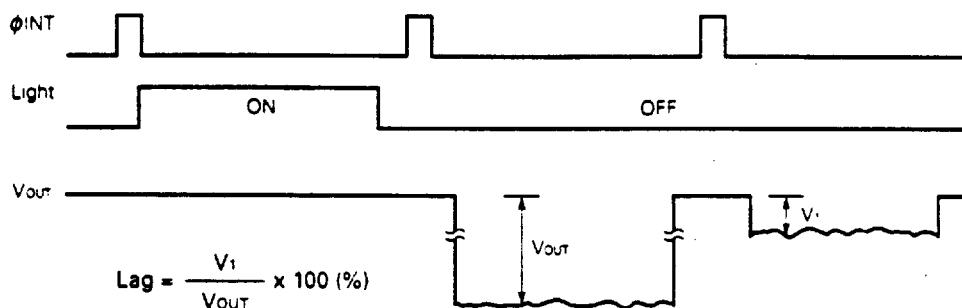
7. Response: R

Output voltage divided by exposure ($I_x \cdot s$).

Note that the response varies with the light source.

8. Image Lag: IL

The rate between the last output voltage and the next one after read out the data of a line.



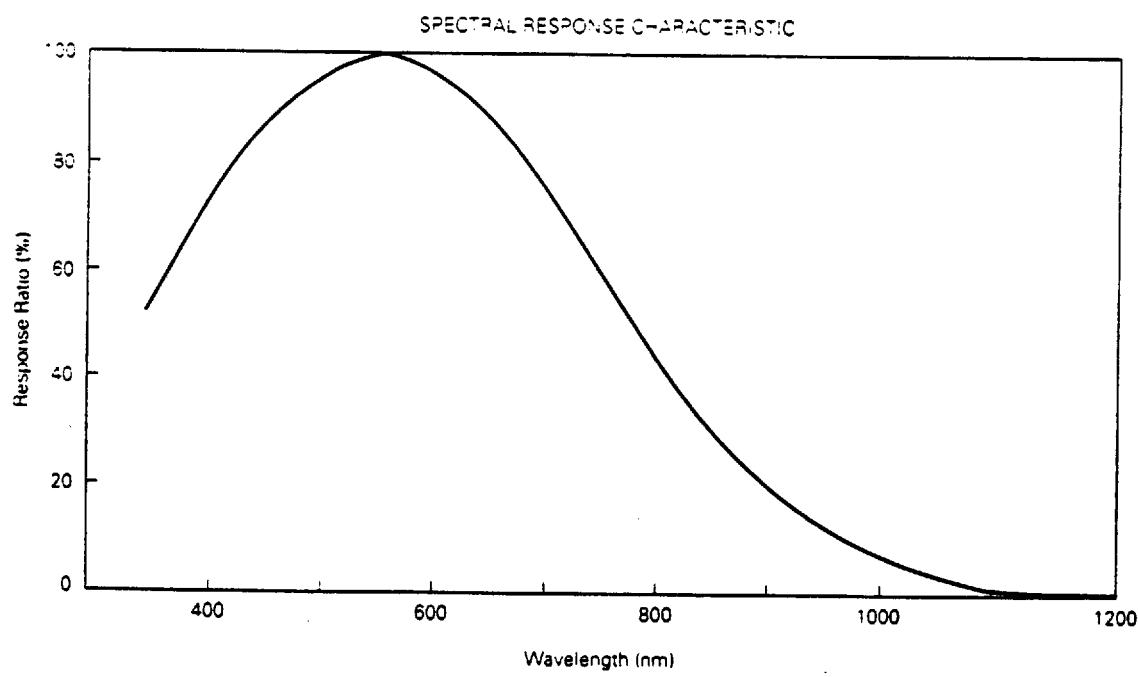
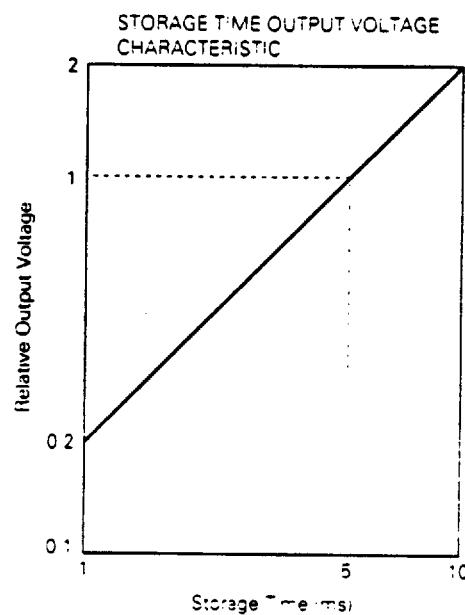
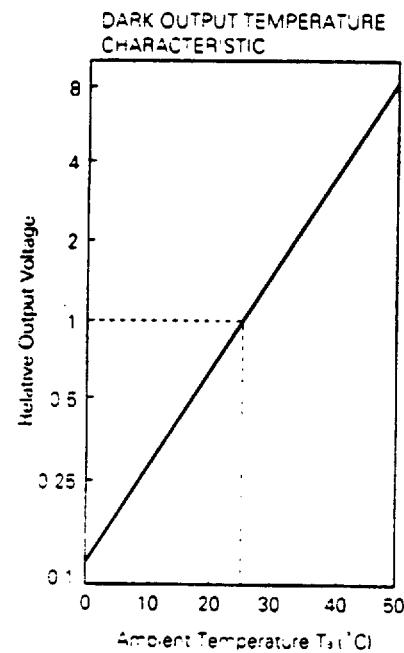
9. Register Imbalance: RI

The rate of the average voltage which is the difference between the output voltage of Odd and Even bits, against the average output voltage of all the valid bits.

$$RI = \frac{\frac{1}{n} \sum_{j=1}^n |V_j - V_{j-1}|}{\frac{1}{n} \sum_{j=1}^n V_j} \times 100 (\%)$$

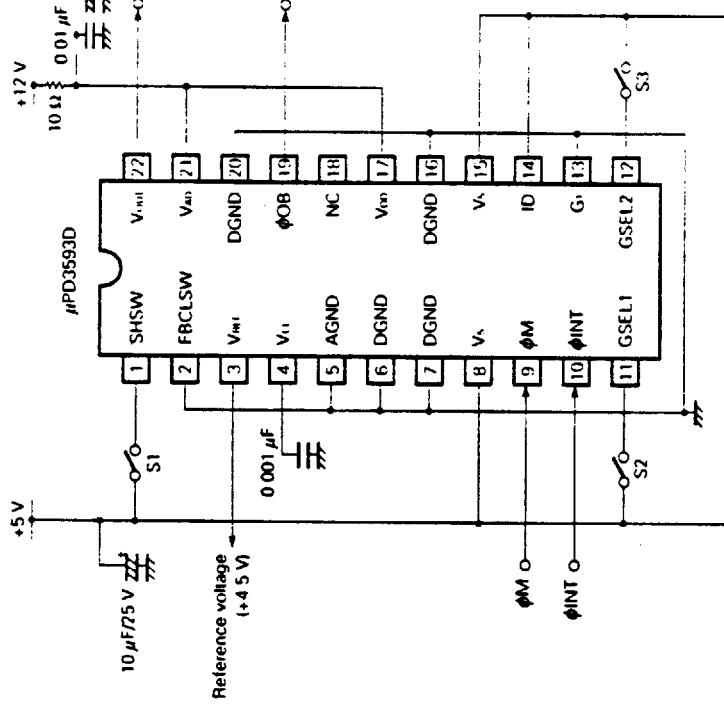
10. Clamp Error: VERR

$V_{ERR} = OB \text{ unit offset voltage} - V_{REF}$

STANDARD CHARACTERISTIC CURVES ($T_o = 25^\circ\text{C}$)

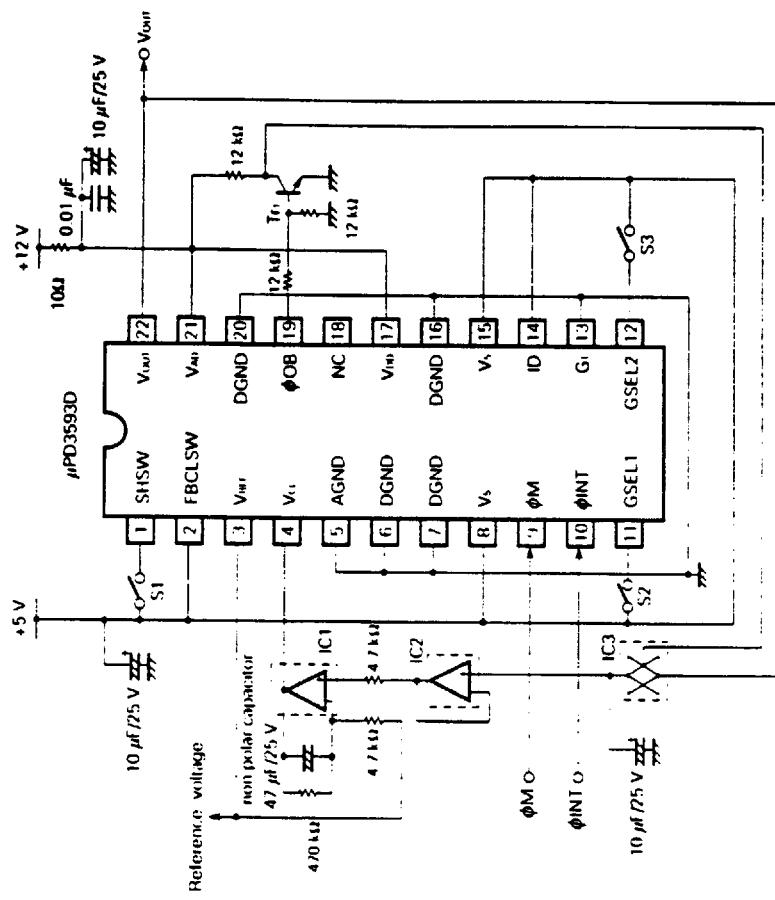
APPLICATION EXAMPLES

Example 1: With internal feedback clamp



- S1: Sample and hold circuit use/unuse select switch
[OFF; Use ON; Unused]
S2, S3: Output amplifier gain select switch

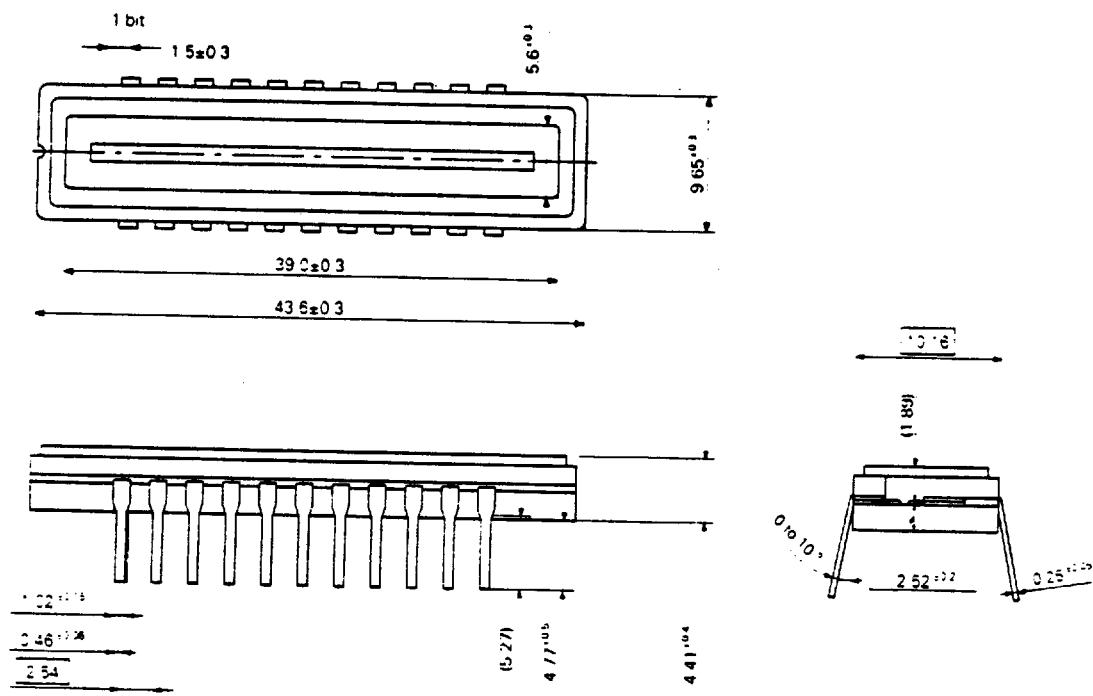
Example 2: Without internal feedback clamp



- IC1, IC2: Low offset, low input current
IC3: μPD4066
Tr1: 2SC945

The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

PACKAGE DIMENSIONS (Unit: mm)



Name	Dimensions	Refractive index
Glass cap	42.2 x 9.0 x 0.5	1.5